

D2 9. (Amended) The method of claim 1 wherein the slurry has a selectivity that falls within an approximate range of 0.9-1.1:1.

D3 17. (Amended) The method of claim 1 wherein the second layer of material is thicker than the layer of first material.

D4 22. (Twice Amended) A method of planarizing a layer of semiconductor material on a processed wafer, the wafer having a top surface, the top surface having a wafer lower level and a wafer upper level that lies above the wafer lower level, the method comprising the steps of:

forming a layer of first material on the top surface of the wafer, the layer of first material having a top surface, the top surface of the layer of first material having a first lower level and a first upper level that lies above the first lower level;

forming a layer of second material on the top surface of the layer of first material; and chemically-mechanically polishing the layer of second material and the underlying layer of first material until the layer of first material is substantially planar to form a planarized layer of first material, the planarized layer of first material covering the wafer upper level of the top surface of the wafer; and

forming a layer of third material on the planarized layer of first material, the third layer of material lowering a resistance of the first layer of material.

Please add the following new claims:

D5 --24. A method of forming a planarized layer of material on a processed wafer, the wafer having a top surface, the top surface having spaced-apart wafer upper levels and a wafer lower level that lies between the wafer upper levels, the wafer upper levels lying above the wafer lower level, the method comprising the steps of:

forming a layer of first material on the top surface of the wafer, the layer of first material having a top surface, the top surface of the layer of first material having a first lower level and a first upper level that lies above the first lower level;

forming a layer of second material on the top surface of the layer of first material;  
chemically-mechanically polishing the layer of second material and the underlying  
layer of first material until the layer of first material is substantially planar to form a  
planarized layer of material, the planarized layer of material covering the wafer upper levels  
and the wafer lower level of the top surface of the wafer; and

selectively etching the planarized layer of material that covers the wafer upper levels  
and the wafer lower level of the top surface of the wafer.

25. The method of claim 24 and further comprising the step of forming a layer of  
third material on the planarized layer of material, the layer of third material and the layer of  
first material being selectively etched during the selectively etching step.

26. The method of claim 25 wherein the layer of third material is conductive.

27. The method of claim 24 wherein the layer of first material and the layer of  
second material are etched with a slurry that etches the layer of first material and the layer of  
second material at approximately a same rate.

28. The method of claim 24 wherein all of the layer of second material is removed  
during the chemically-mechanically polishing step.--